

250V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS}=250V$; $R_{DS(ON)}=8.5\Omega$; $I_D=310mA$

DESCRIPTION

This 250V enhancement mode N-channel MOSFET provides users with a competitive specification offering efficient power handling capability, high impedance and is free from thermal runaway and thermally induced secondary breakdown. Applications benefiting from this device include a variety of Telecom and general high voltage circuits.

SOT89 and SOT23-6 versions are also available.

FEATURES

- High voltage
- Low on-resistance
- Fast switching speed
- Low gate drive
- Low threshold
- Complementary P-channel Type ZVP4525G
- SOT223 package

APPLICATIONS

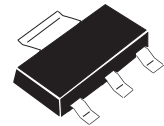
- Earth Recall and dialling switches
- Electronic hook switches
- High Voltage Power MOSFET Drivers
- Telecom call routers
- Solid state relays

ORDERING INFORMATION

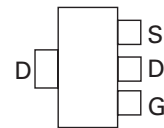
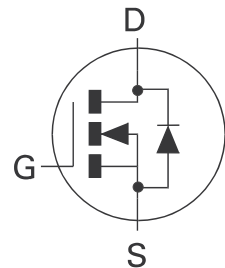
DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZVN4525GTA	7	8mm embossed	1000 units
ZVN4525GTC	13	8mm embossed	4000 units

DEVICE MARKING

- ZVN4525G



SOT223



Top View

ZVN4525G

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	250	V
Gate Source Voltage	V_{GS}	± 40	V
Continuous Drain Current ($V_{GS}=10V$; $T_A=25^\circ C$)(a) ($V_{GS}=10V$; $T_A=70^\circ C$)(a)	I_D	310	mA
	I_D	248	mA
Pulsed Drain Current (c)	I_{DM}	1.44	A
Continuous Source Current (Body Diode)	I_S	1.1	A
Pulsed Source Current (Body Diode)	I_{SM}	1.44	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	2	W
		16	mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	63	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	26	$^\circ C/W$

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

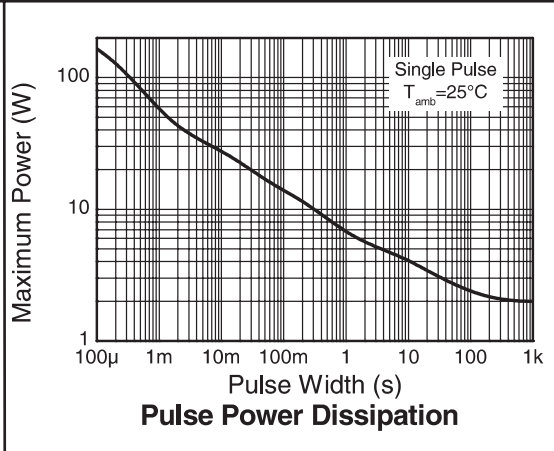
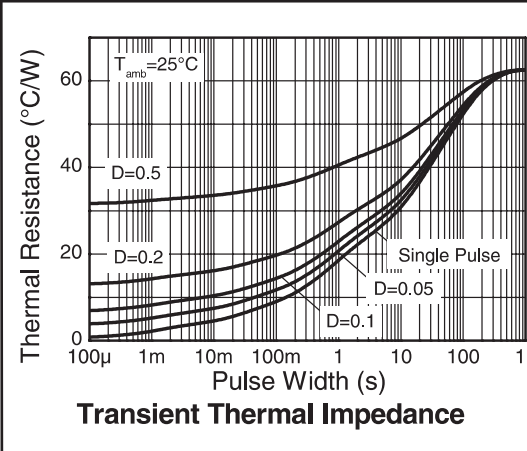
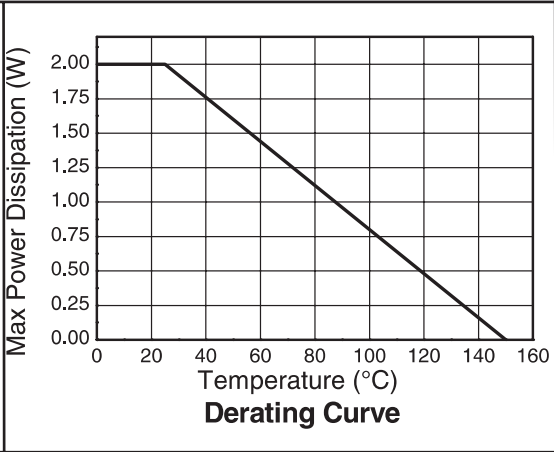
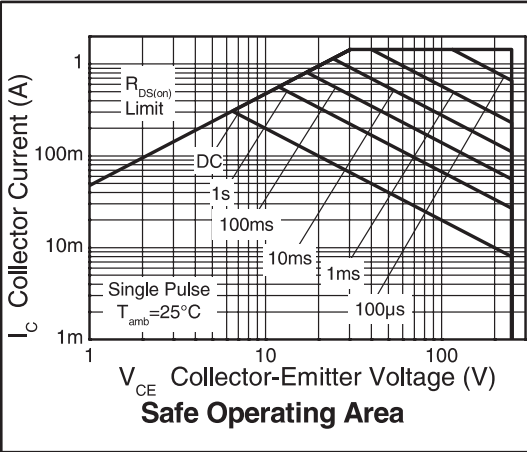
(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal

NB High Voltage Applications

For high voltage applications, the appropriate industry sector guidelines should be considered with regard to voltage spacing between conductors.

CHARACTERISTICS



ZVN4525G

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

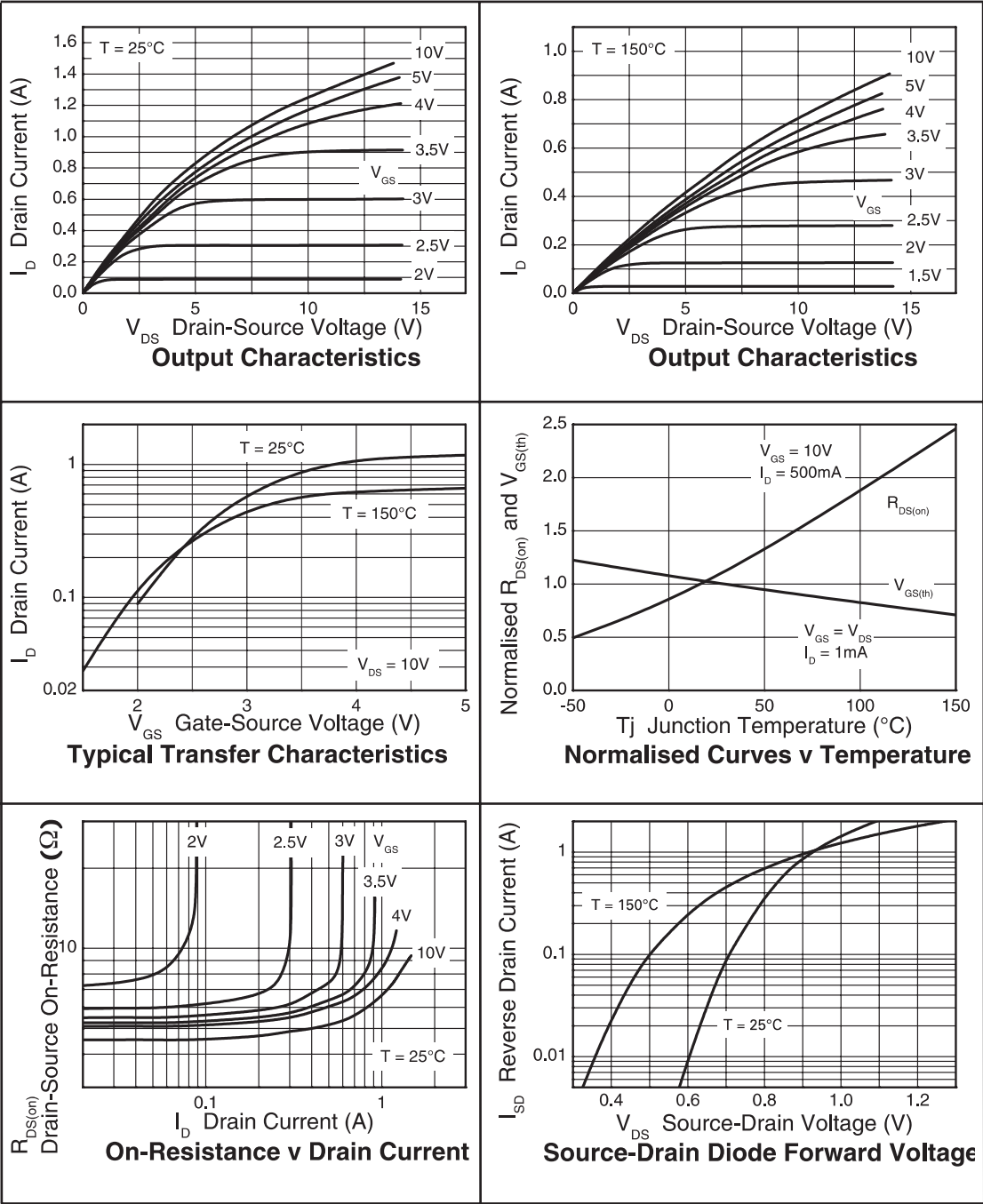
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNI T	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	250	285		V	$I_D=1\text{mA}, V_{GS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}		35	500	nA	$V_{DS}=250\text{V}, V_{GS}=0\text{V}$
Gate-Body Leakage	I_{GSS}		± 1	± 100	nA	$V_{GS}=\pm 40\text{V}, V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	1.4	1.8	V	$I_D=1\text{mA}, V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		5.6 5.9 6.4	8.5 9.0 9.5	Ω	$V_{GS}=10\text{V}, I_D=500\text{mA}$ $V_{GS}=4.5\text{V}, I_D=360\text{mA}$ $V_{GS}=2.4\text{V}, I_D=20\text{mA}$
Forward Transconductance (3)	g_{fs}	0.3	0.475		S	$V_{DS}=10\text{V}, I_D=0.3\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		72		pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}$
Output Capacitance	C_{oss}		11		pF	
Reverse Transfer Capacitance	C_{rss}		3.6		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		1.25		ns	$V_{DD}=30\text{V}, I_D=360\text{mA}$ $R_G=50\Omega, V_{GS}=10\text{V}$ (refer to test circuit)
Rise Time	t_r		1.70		ns	
Turn-Off Delay Time	$t_{d(off)}$		11.40		ns	
Fall Time	t_f		3.50		ns	
Total Gate Charge	Q_g		2.6	3.65	nC	$V_{DS}=25\text{V}, V_{GS}=10\text{V},$ $I_D=360\text{mA}$ (refer to test circuit)
Gate-Source Charge	Q_{gs}		0.2	0.28	nC	
Gate Drain Charge	Q_{gd}		0.5	0.70	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			0.97	V	$T_j=25^{\circ}\text{C}, I_S=360\text{mA},$ $V_{GS}=0\text{V}$
Reverse Recovery Time (3)	t_{rr}		186	260	ns	$T_j=25^{\circ}\text{C}, I_F=360\text{mA},$ $di/dt= 100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	Q_{rr}		34	48	nC	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.

(2) Switching characteristics are independent of operating junction temperature.

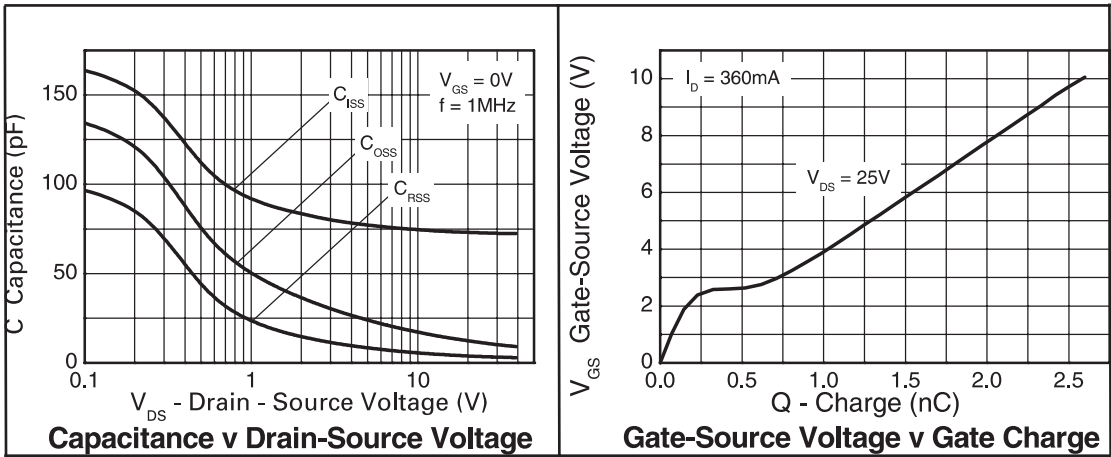
(3) For design aid only, not subject to production testing.

TYPICAL CHARACTERISTICS

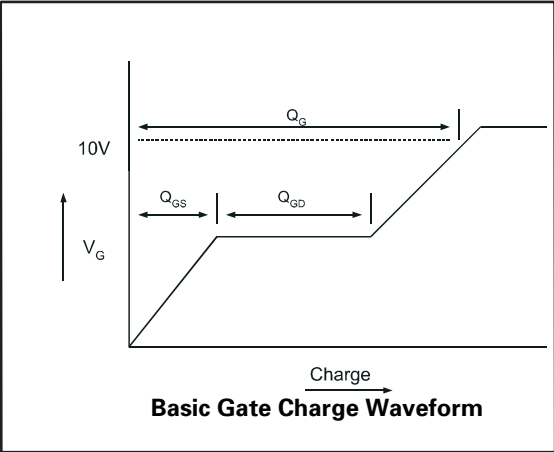


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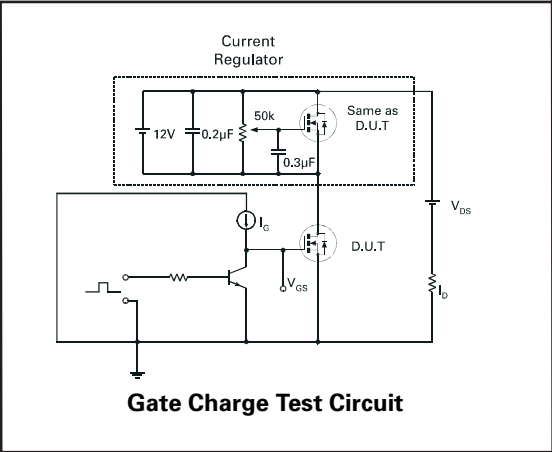
CHARACTERISTICS



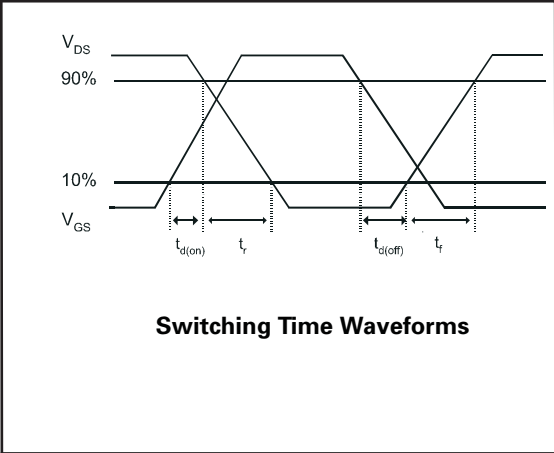
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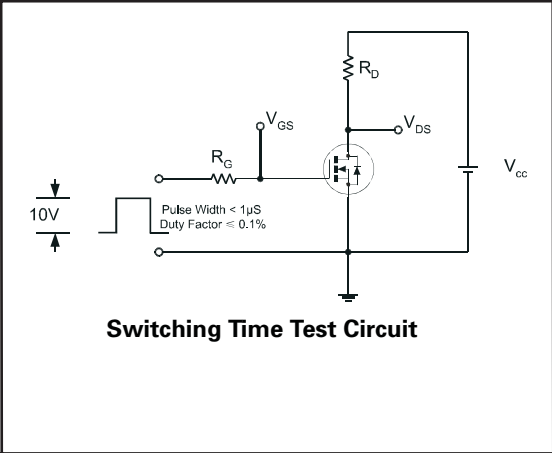
Basic Gate Charge Waveform



Gate Charge Test Circuit



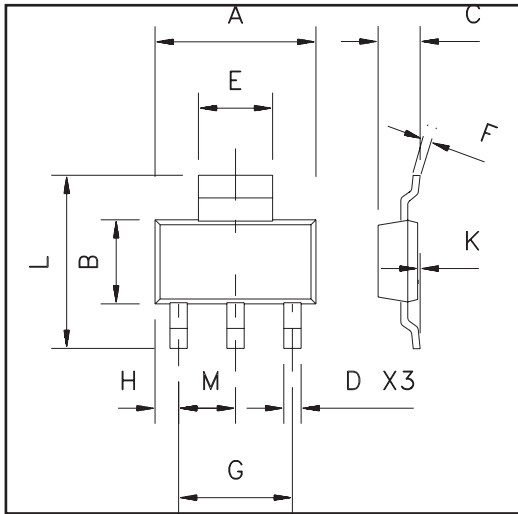
Switching Time Waveforms



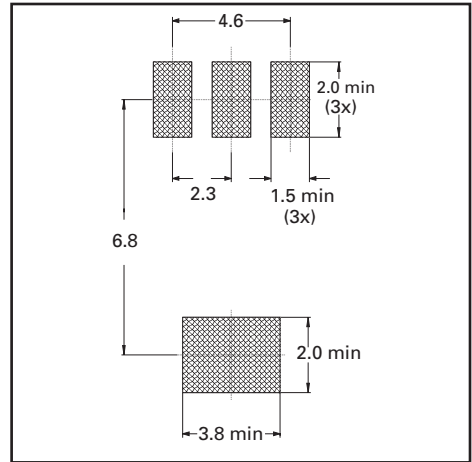
Switching Time Test Circuit

ZVN4525G

PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	6.3	6.7	0.248	0.264
B	3.3	3.7	0.130	0.146
C	-	1.7	-	0.067
D	0.6	0.8	0.024	0.031
E	2.9	3.1	0.114	0.122
F	0.24	0.32	0.009	0.013
G	NOM 4.6		NOM 0.181	
H	0.85	1.05	0.033	0.041
K	0.02	0.10	0.0008	0.004
L	6.7	7.3	0.264	0.287
M	NOM 2.3		NOM 0.0905	



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